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Reinmuth

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(54) **MICROELECTROMECHANICAL COMPONENT AND MANUFACTURING METHOD FOR MICROELECTROMECHANICAL COMPONENTS**

(71) Applicant: **Robert Bosch GmbH**, Stuttgart (DE)

(72) Inventor: **Jochen Reinmuth**, Reutlingen (DE)

(73) Assignee: **ROBERT BOSCH GMBH**, Stuttgart (DE)

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See application file for complete search history.

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Primary Examiner — Shaun Campbell

(74) *Attorney, Agent, or Firm* — Norton Rose Fulbright US LLP

(57) **ABSTRACT**

An MEMS component includes: a substrate into which a cavity is structured from a functional top side; a buried polysilicon layer in which a polysilicon diaphragm which at least partially spans the cavity is exposed as the first electrode; an epi-polysilicon layer in which a conductive structure, which is situated at a distance above the polysilicon diaphragm by a clearance, is exposed as the second electrode; and an access opening which fluidically connects the external surroundings of the MEMS component to the cavity. At least one access channel is formed in at least one of the buried polysilicon layer, the epi-polysilicon layer, and an inner wall of the cavity of the substrate which connects the access opening to the cavity, and whose channel width is not greater than 5 μm.

4 Claims, 29 Drawing Sheets

